

L Number	Hits	Search Text	DB	Time stamp
-	130	(corning near1 7059\$1 near2 glass adj substrate) and thin adj film adj transistor	USPAT	2002/06/14 16:39
-	566	thin adj film adj transistor and top adj gate	USPAT	2002/06/12 13:00
-	2	thin adj film adj transistor and multilayer adj gate adj insulat\$3	USPAT	2002/06/12 13:02
-	7	thin adj film adj transistor and multi\$1layer\$2 adj gate adj insulat\$3	USPAT	2002/06/12 13:04
-	4	thin adj film adj transistor and multi\$1layer\$2 adj gate adj insulat\$3	US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/06/12 13:06
-	1428	(257/59, 64, 65, 66, 70, 75).CCLS.	USPAT	2002/06/12 13:54
-	74	((257/410, 411).CCLS.) and thin adj film adj transistor	USPAT	2002/06/12 14:28
-	120	(257/406, 407).CCLS.	USPAT	2002/06/12 14:49
-	7	((257/406, 407).CCLS.) and silicon adj oxynitride	USPAT	2002/06/12 14:49
-	510	(257/410, 411).CCLS.	USPAT	2002/06/12 16:06
-	7	("4442449" "5241214" "5250818" "5461250" "5468987" "5561302" "5602403").PN.	USPAT	2002/06/12 14:55
-	2	jp-08195494-\$.did.	JPO; DERWENT USPAT;	2002/06/12 16:07
-	21	thin adj film adj transistor and gate near2 oxynitride	US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/06/14 15:08
-	9	thin adj film adj transistor and gate near2 oxynitride	USPAT; IBM_TDB	2002/06/14 15:14
-	3	thin adj film adj transistor and gate near2 silicon adj oxynitride	USPAT; IBM_TDB USPAT	2002/06/14 15:14
-	861	(257/347).CCLS.	USPAT	2002/06/14 16:39